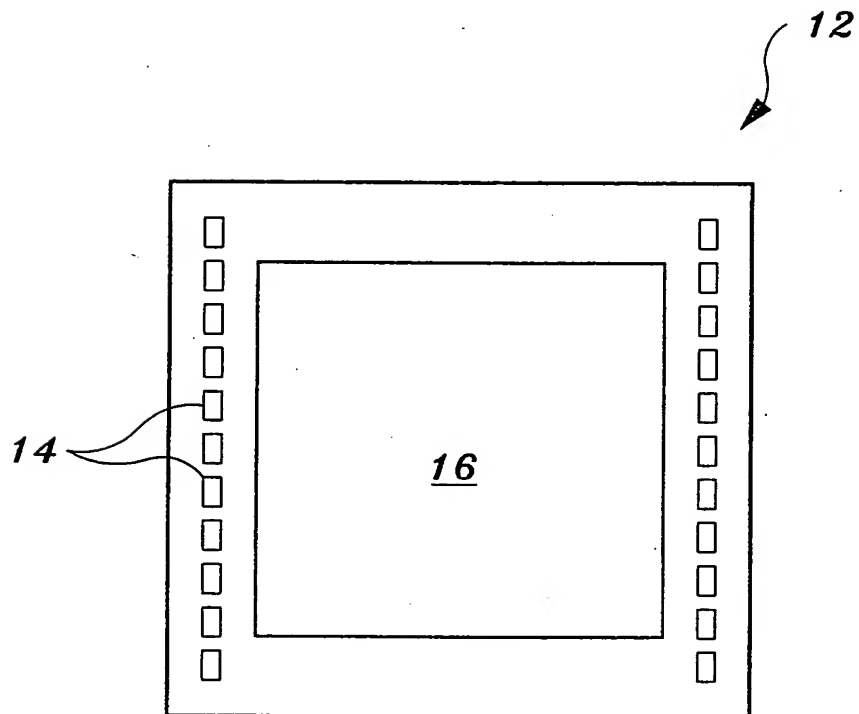
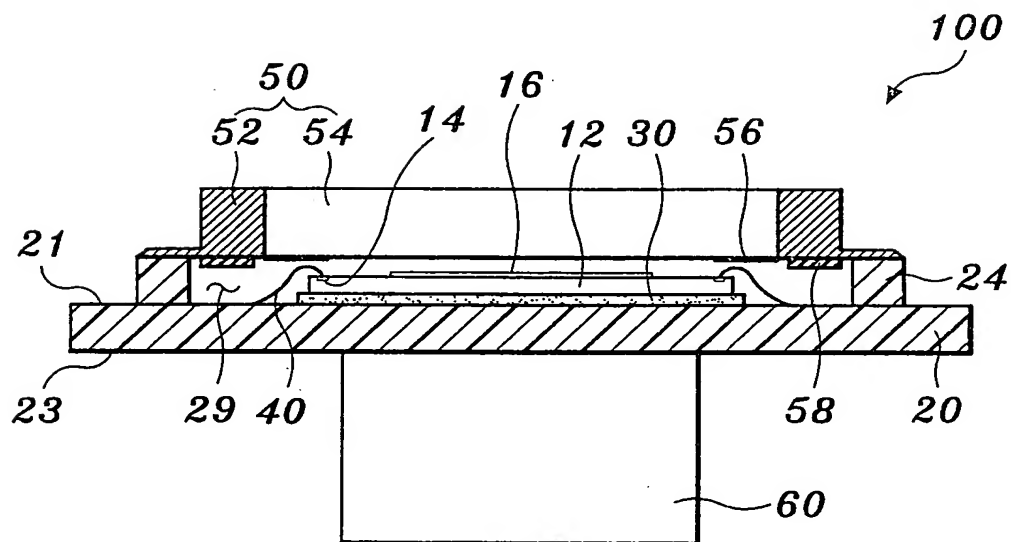


**FIG. 1**  
( *Prior Art* )

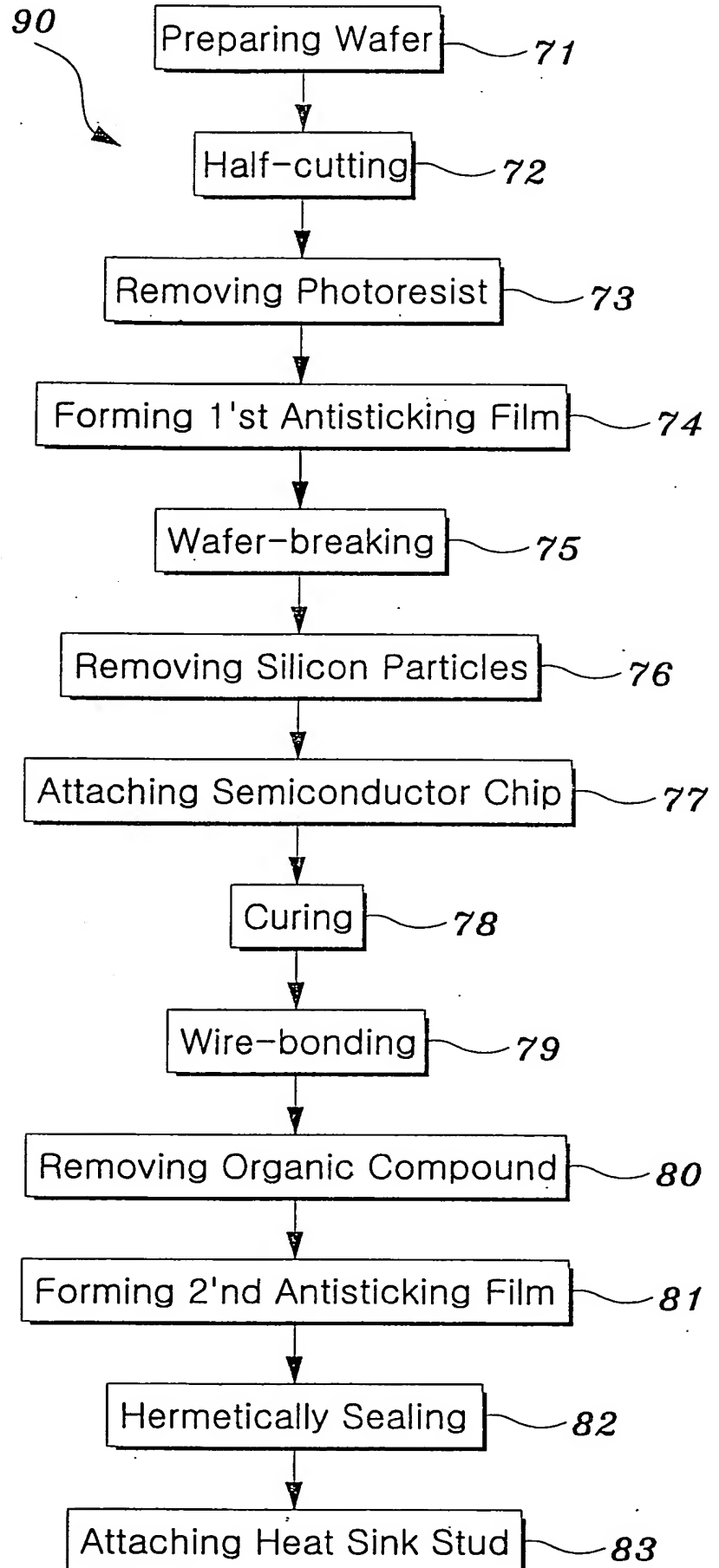


**FIG. 2**  
( Prior Art )

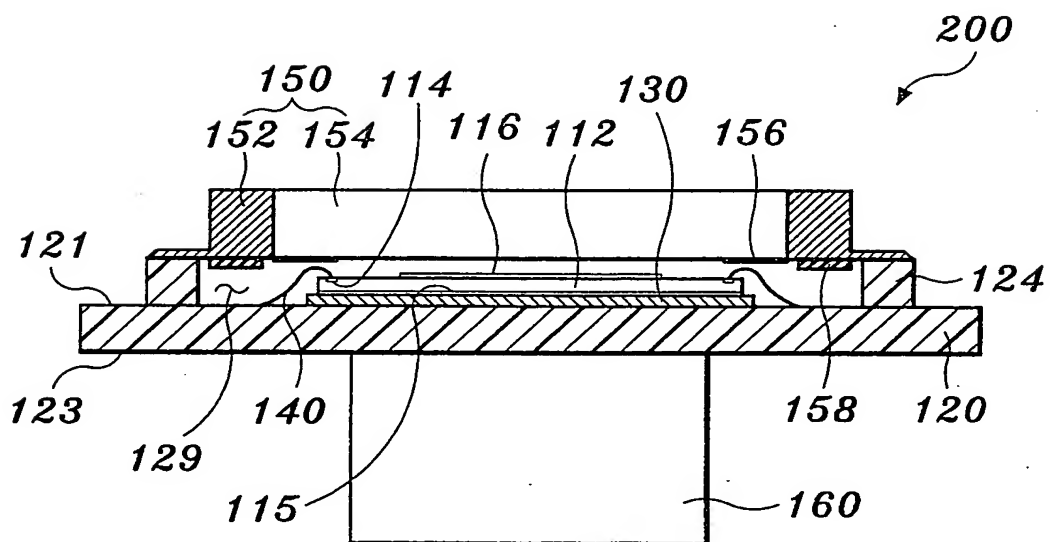


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**FIG. 3**  
( Prior Art )

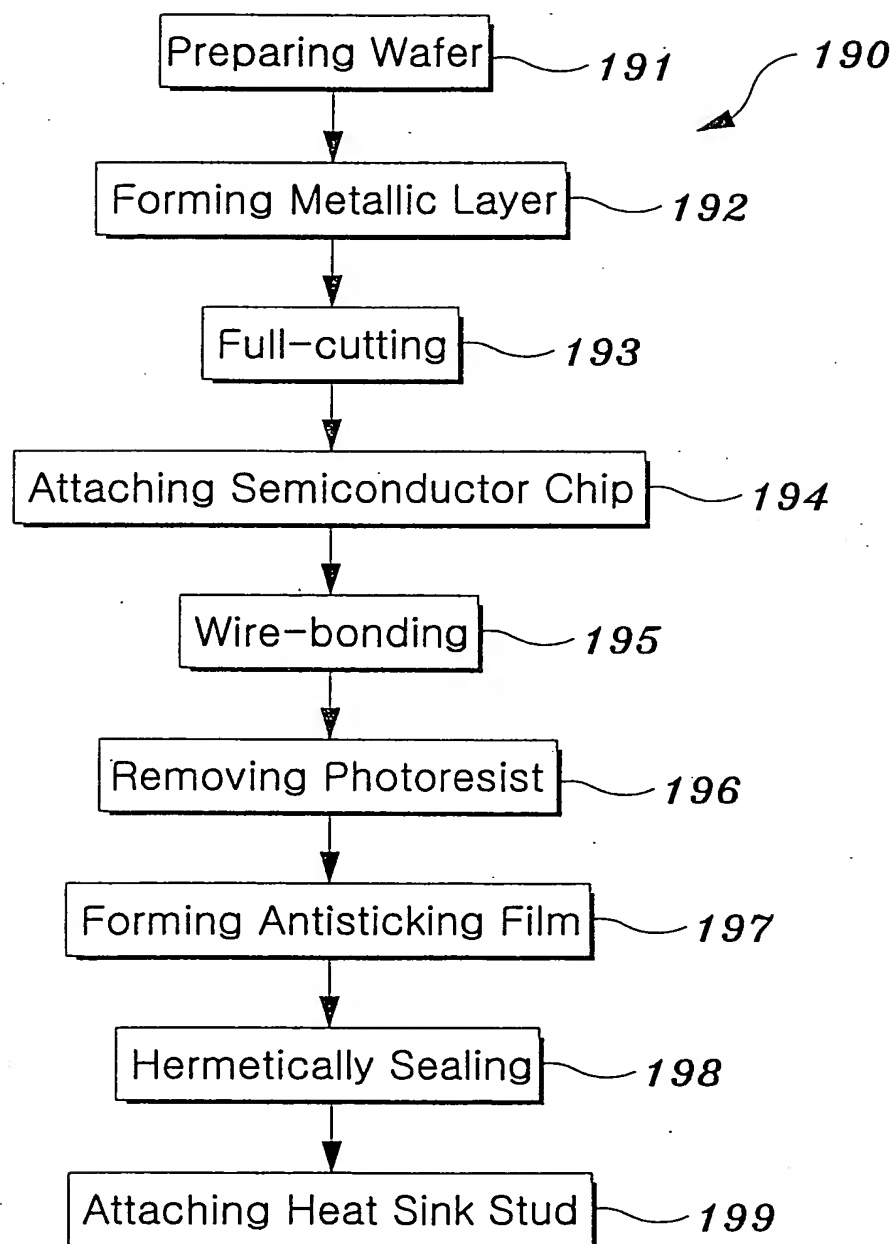


*FIG. 4*

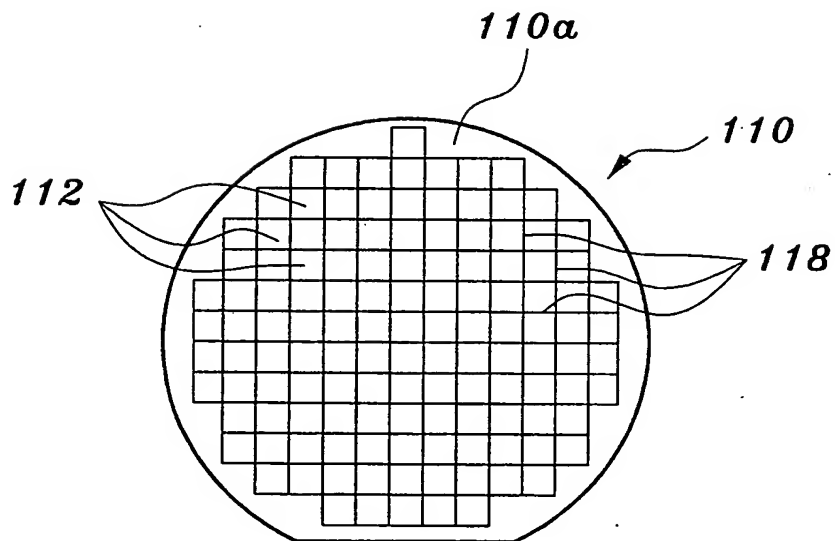


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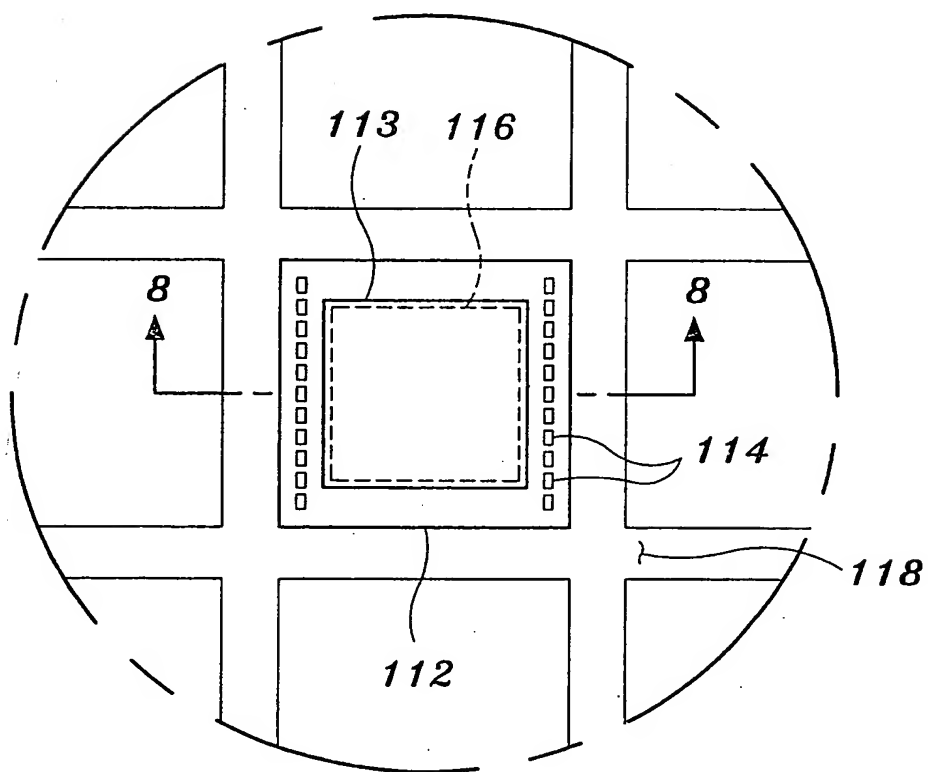
*FIG. 5*



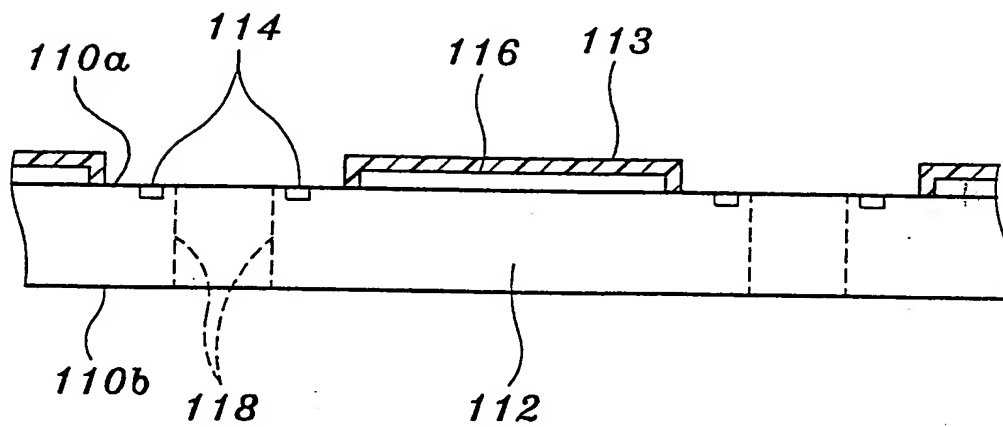
**FIG. 6**



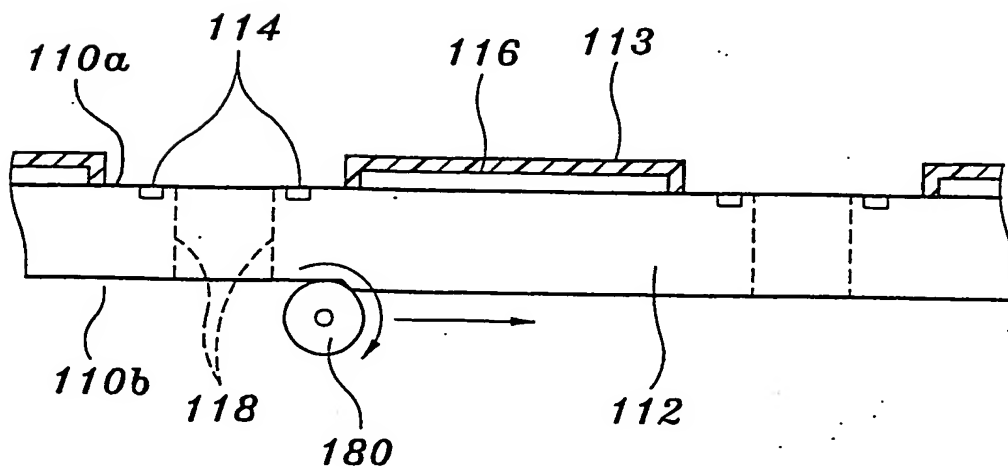
*FIG. 7*



*FIG. 8*



*FIG. 9*

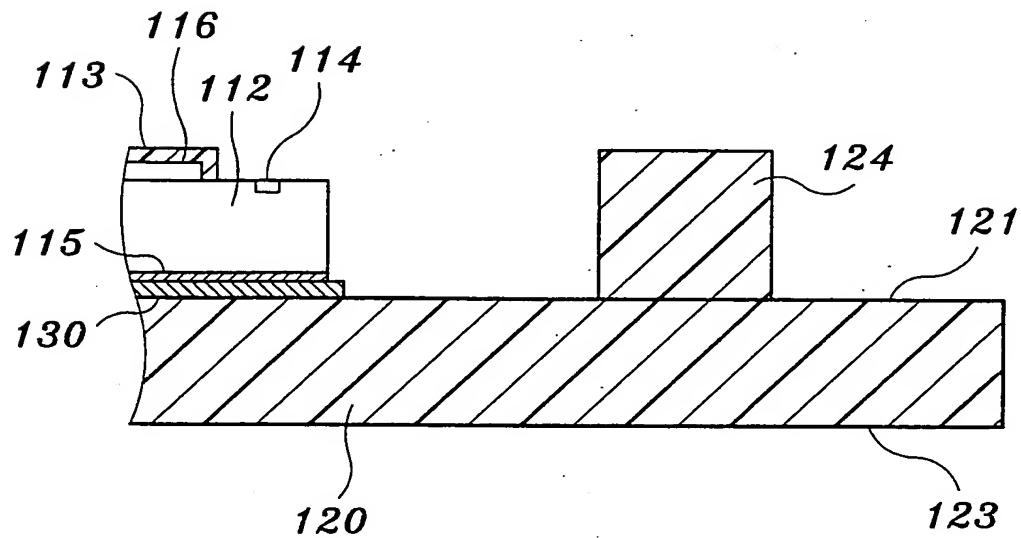




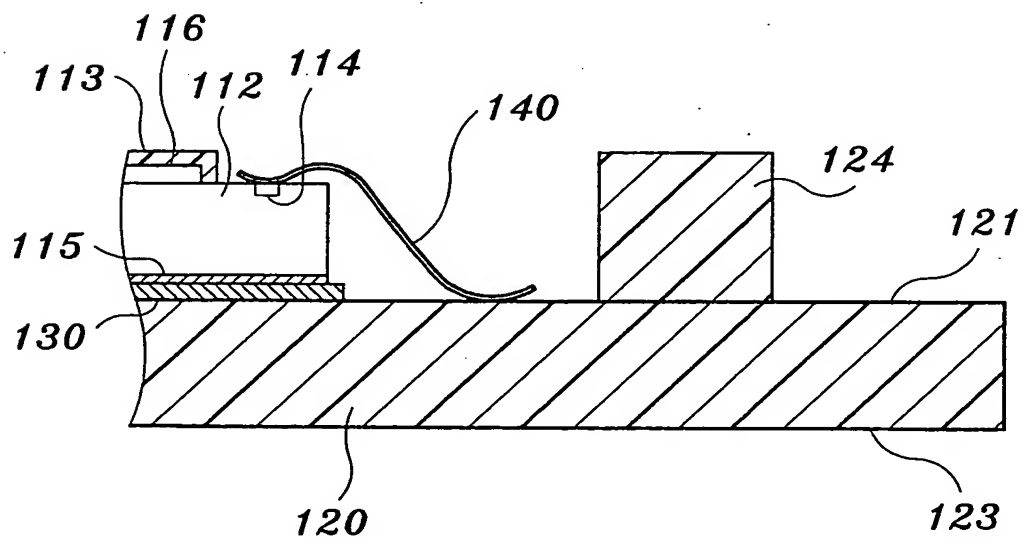
This cross-sectional view shows a central channel region 112 flanked by side regions 110a and 110b. A gate stack 113 is positioned on top of the channel region 112. A vertical structure 170 is located on the right side of the channel region 112. The device is formed on a substrate 115. Various other components are labeled with reference numerals 110a, 110b, 111a, 111b, 112, 113, 114, 115, 116, 117, 118, and 119.

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*FIG. 12*

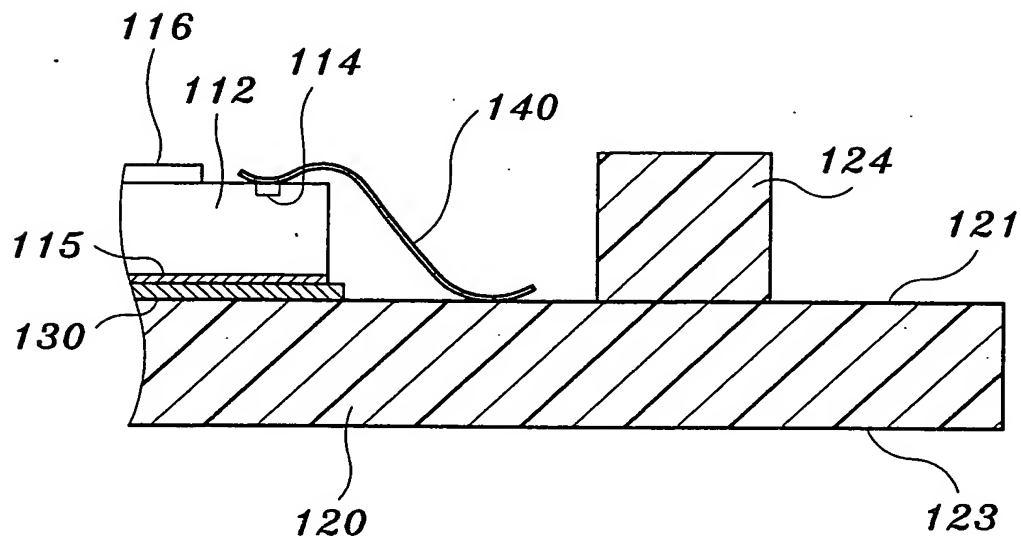


*FIG. 13*



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*FIG. 14*



*FIG. 15*

